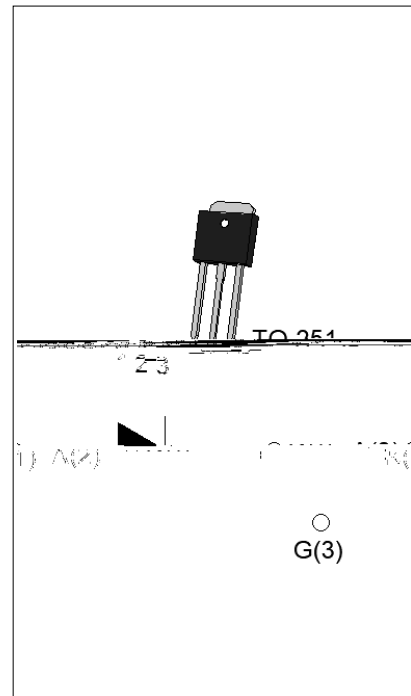




DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT812H of silicon controlled rectifiers provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. Package TO-251 is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM}/V_{RRM}	800	V
I_{GT}	15	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	800	V
Average on-state current ($T_c=63^\circ\text{C}$)	$I_{T(AV)}$	7.6	A
RMS on-state current ($T_c=63^\circ\text{C}$)	$I_{T(RMS)}$	12	A
Non repetitive surge peak on-state current ($t_p=10\text{ms}, T_j=25^\circ\text{C}$)	I_{TSM}	140	A
Non repetitive surge peak on-state current ($t_p=8.3\text{ms}, T_j=25^\circ\text{C}$)		154	
I^2t value for fusing ($t_p=10\text{ms}, T_j=25^\circ\text{C}$)	I^2t	98	A^2s
Critical rate of rise of on-state current ($I_G=2 I_{GT}, f=100\text{Hz}, T_j=125^\circ\text{C}$)	di/dt	150	$\text{A}/\mu\text{s}$
Peak gate current ($t_p=20\mu\text{s}, T_j=125^\circ\text{C}$)	I_{GM}	4	A

Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	0.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V$ $R_L=33$	-	-	15	mA
V_{GT}		-	-	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k$	0.2	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	60	mA
I_H	$I_T=500mA$	-	-	50	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125$	500	-	-	V/ μs
t_{on}	$I_G=20mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25$	-	5	-	μs
t_{off}		-	80	-	

STATIC CHARACTERISTICS
20

JCT812H

 **JieJie Microelectronics Co., Ltd.**

ORDERING INFORMATION

JCT812H

FIG.1: Maximum power dissipation versus RMS on-state current



FIG.2: RMS on-state current versus case temperature

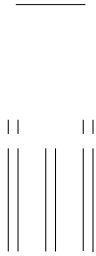
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT812H	800	15	TO-251	80	Tube

Document Revision History

Date	Revision	Changes
Apr.13, 2023	A.1.0	Last update
Oct.16, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

PACKAGE MECHANICAL DATA



JCT812H

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